



BC857BS

PNP GENERAL PURPOSE DUALTRANSISTORS

VOLTAGE 45 Volts **POWER** 150 mWatts

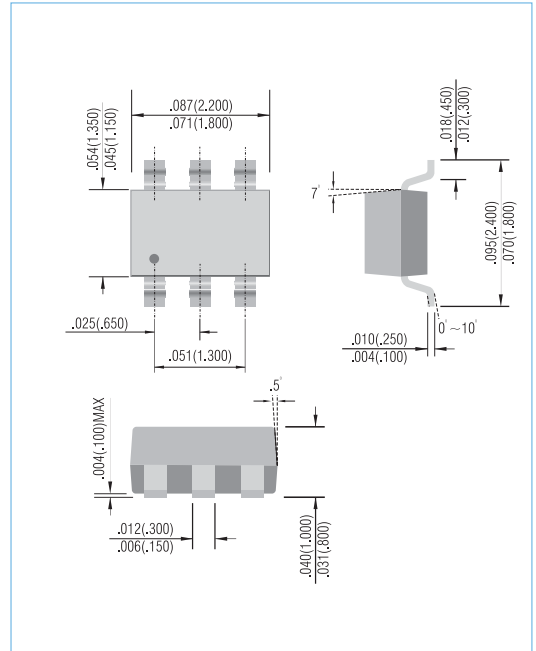
SOT-363 Unit: inch (mm)

FEATURES

- General purpose amplifier applications
- NPN epitaxial silicon, planar design
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

- Case: SOT-363, Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.008 gram
- Marking : 57S



ABSOLUTE MAXIMUM RATINGS

PARAMETER	Symbol	Value	Units
Collector - Emitter Voltage	V_{CE0}	-45	V
Collector - Base Voltage	V_{CB0}	-50	V
Emitter - Base Voltage	V_{EB0}	-5.0	V
Collector Current - Continuous	I_C	100	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A=25^{\circ}C$ Derate above 25°C	P_D	300 150 3.0	mW mW/°C
Thermal Resistance , Junction to Ambient	$R_{\theta JA}$	328	°C/W
Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C

Note 1: FR-4 board 70 x 60 x 1mm.



BC857BS

ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise noted)

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Unit
OFF CHARACTERISTICS						
Collector - Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA	-45	-	-	V
Collector - Emitter Breakdown Voltage	V _{(BR)CES}	I _C =10μA, V _{EB} =0	-50	-	-	
Collector - Base Breakdown Voltage	V _{(BR)CBO}	I _C =10μA	-50	-	-	V
Emitter - Base Breakdown Voltage	V _{(BR)EBO}	I _E =10μA	-5.0	-	-	V
Collector Cutoff Current	I _{CBO}	V _{CB} =30V, V _{CB} =30V, T _A =150°C	-	-	-15 -5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain	h _{FE}	I _C =10μA, V _{CE} =5V	200 420	150	- -	-
DC Current Gain	h _{FE}	I _C =2.0mA, V _{CE} =5V	- -	150	475 800	-
Collector - Emitter Saturation Voltage	V _{CE(SAT)}	I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5.0mA	-	-	-0.25 -0.6	V
Base - Emitter Saturation Voltage	V _{BE(SAT)}	I _C =10mA, I _B =0.5mA I _C =100mA, I _B =5.0mA	- -	-0.7 -0.9	- -	V
Base - Emitter Voltage	V _{BE(SAT)}	I _C =2mA, V _{CE} =5.0V I _C =10mA, V _{CE} =5.0V	-580 -	-660 -	-700 -770	mV
SMALL-SIGNAL CHARACTERISTICS						
Current-Gain-Bandwidth Product	f _T	I _C =10mA, V _{CE} =5.0Vdc, f=100MHz	100	-	-	MHz
Output Capacitance	C _{ob0}	V _{CB} =10V, f=1.0MHz	-	-	4.5	pF
Noise Figure	NF	I _C =0.2mA, V _{CE} =5.0Vdc, R _S =2.0kΩ, f=1.0kHz, BW=200Hz	-	-	10	dB

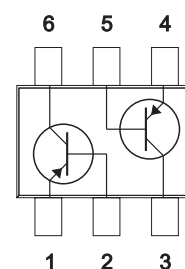


Fig.53



BC857BS

ELECTRICAL CHARACTERISTICS CURVE

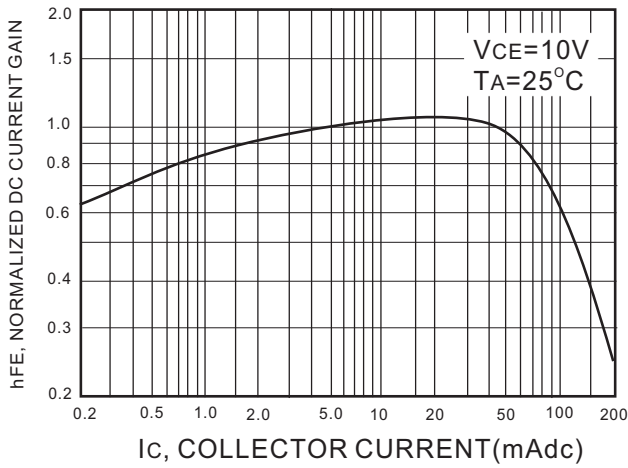


Figure 1. Normalized DC Current Gain

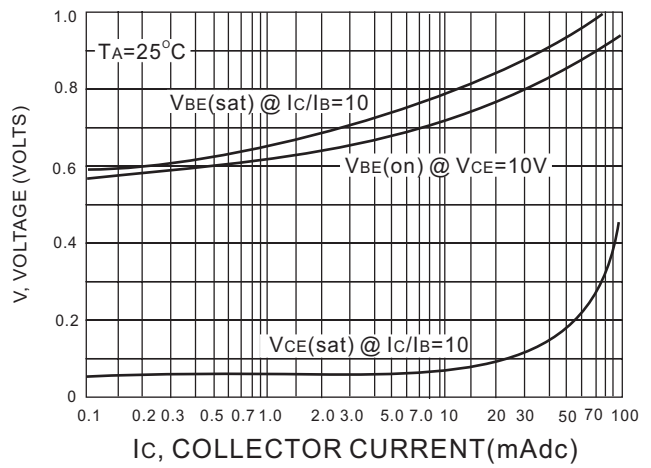


Figure 2. "Saturation" and "On" Voltages

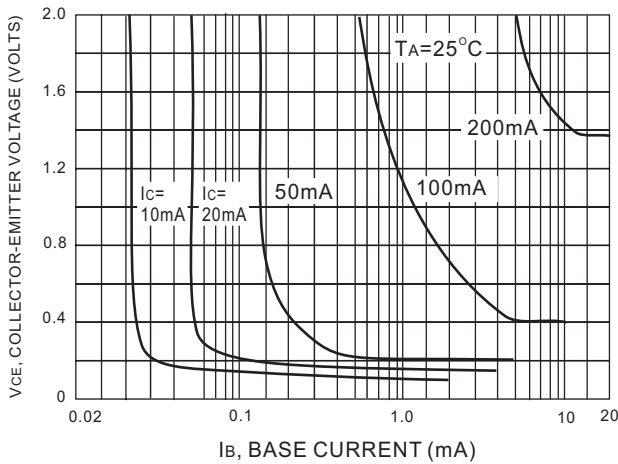


Figure 3. Collector Saturation Region

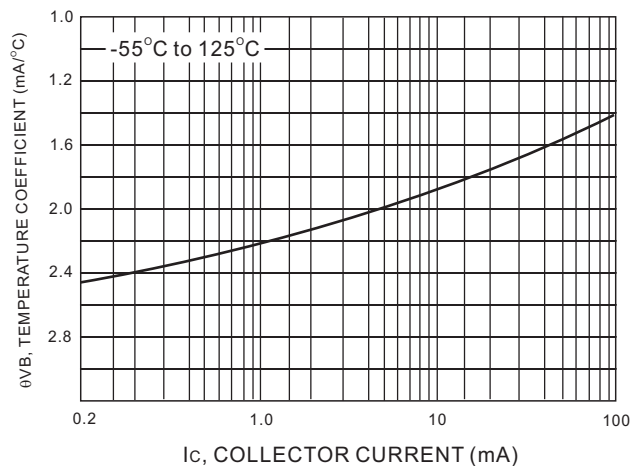


Figure 4. Base-Emitter Temperature Coefficient

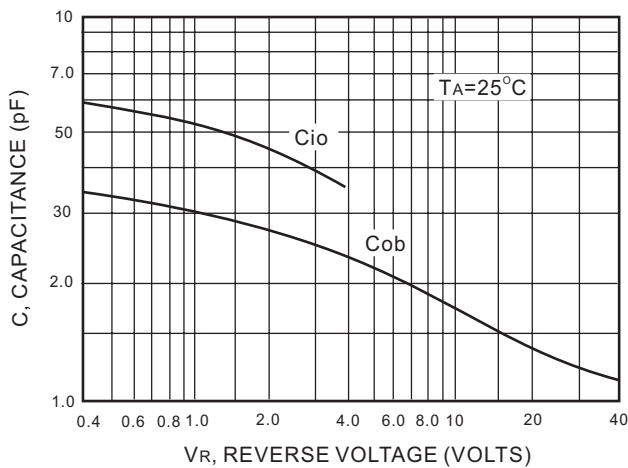


Figure 5. Capacitance

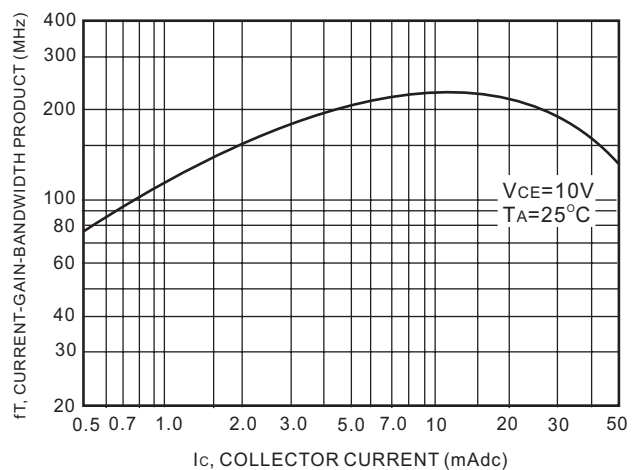
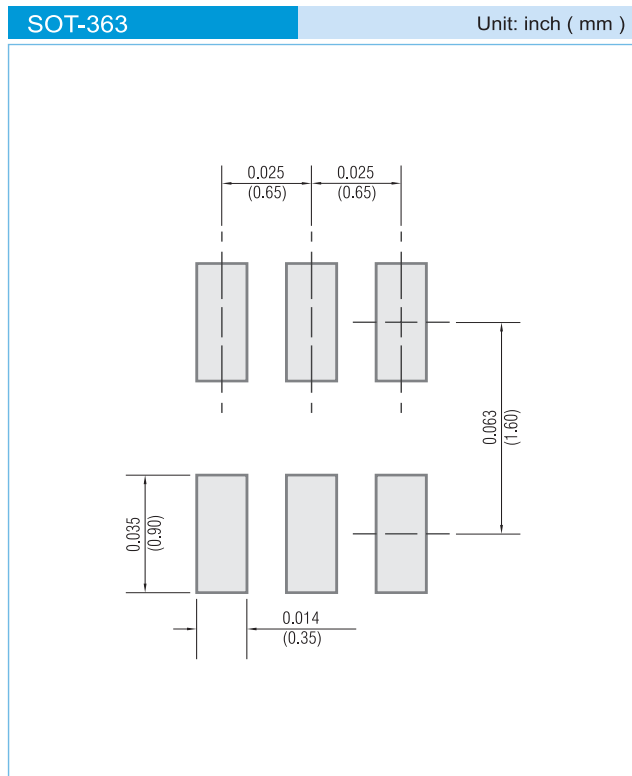


Figure 6. Current-Gain-Bandwidth Product



BC857BS

MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information

T/R - 10K per 13" plastic Reel

T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

Copyright PanJit International, Inc 2009

The information presented in this document is believed to be accurate and reliable. The specifications and information herein are subject to change without notice. Pan Jit makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. Pan Jit products are not authorized for use in life support devices or systems. Pan Jit does not convey any license under its patent rights or rights of others.